



IXTQ150N06P Information

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Part Number IXTQ150N06P

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 150A TO-3P

Package TO-3P-3, SC-65-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXTQ150N06P Specifications

Manufacturer Part Number IXTQ150N06P Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-3P-3, SC-65-3 Series PolarHT? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 150A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 118nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 480W (Tc) Rds On (Max) @ Id, Vgs 10 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P-3, SC-65-3 Package / Case TO-3P-3, SC-65-3		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C150A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs118nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Package	TO-3P-3, SC-65-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C150A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs118nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Series	PolarHT?
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Current - Continuous Drain (Id) @ 25°C150A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs118nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs118nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 118nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 480W (Tc) Rds On (Max) @ Id, Vgs 10 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Current - Continuous Drain (Id) @ 25°C	150A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 75A, 10V Operating Temperature Jenuary Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Gate Charge (Qg) (Max) @ Vgs	118nC @ 10V
FET Feature - Power Dissipation (Max) 480W (Tc) Rds On (Max) @ Id, Vgs 10 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Input Capacitance (Ciss) (Max) @ Vds	3000pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 10 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Power Dissipation (Max)	480W (Tc)
Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Rds On (Max) @ Id, Vgs	10 mOhm @ 75A, 10V
Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-3P-3, SC-65-3	Mounting Type	Through Hole
	Supplier Device Package	TO-3P
Report errors?	Package / Case	TO-3P-3, SC-65-3
		Report errors?

IXTQ150N06P Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTQ150N06P Payment Methods

































If you have any question about IXTQ150N06P, please do not hesitate to contact us!

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